

Title (en)
VACUUM ULTRAVIOLET TRANSMITTING DIRECT DEPOSIT VITRIFIED SILICON OXYFLUORIDE LITHOGRAPHY GLASS PHOTOMASK
BLANKS

Title (de)
VITRIFIZIERTE DIREKTABLAGERUNGS-SILIZIUM-OXYFLUORIDLITHOGRAPHIEGLASFOTOMASKENROHLINGE MIT VAKUUM-
ULTRAVIOLETT-DURCHGLASS

Title (fr)
EBAUCHES DE PHOTOMASQUE EN VERRE POUR LITHOGRAPHIE, A BASE D'OXYFLUORURE DE SILICIUM VITRIFIE, A DEPOT DIRECT,
TRANSMETTANT DES ULTRAVIOLETS EXTREMES

Publication
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Application
EP 01955932 A 20010724

Priority

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- US 27113601 P 20010224

Abstract (en)
[origin: WO0221217A1] High purity direct deposit vitrified silicon oxyfluoride glass suitable for use as a photomask substrates for photolithography applications in the VUV wavelength region below 190 nm is disclosed. The inventive direct deposit vitrified silicon oxyfluoride glass is transmissive at wavelengths around 157 nm, making it particularly useful as a photomask substrate at the 157 nm wavelength region. The inventive photomask substrate is a dry direct deposit vitrified silicon oxyfluoride glass which exhibits very high transmittance in the vacuum ultraviolet (VUV) wavelength region while maintaining the excellent thermal and physical properties generally associated with high purity fused silica. In addition to containing fluorine and having little or no OH content, the inventive direct deposit vitrified silicon oxyfluoride glass suitable for use as a photomask substrate at 157 nm is also characterized by having less than 1×10^{17} molecules/cm³ of molecular hydrogen and low chlorine levels.

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G03F 9/00; **C03B 37/027**; **C03C 3/112**; **C03C 15/00**

IPC 8 full level
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